



PSMN7R0-30YL

N-channel 30 V 7 mΩ logic level MOSFET in LPAK

Rev. 04 — 9 March 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converter
- Motor control
- Server power supplies

1.4 Quick reference data

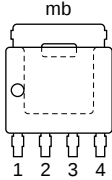
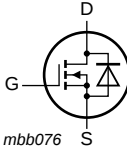
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	-	-	76	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	51	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$	-	4.92	7	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}$; $I_D = 10\text{ A}$;	-	2.9	-	nC
$Q_{G(tot)}$	total gate charge	$V_{DS} = 12\text{ V}$; see Figure 14 ; see Figure 15	-	10	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; $I_D = 65\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ Ω}$; unclamped	-	-	21	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LPAK)

3. Ordering information

Table 3. Ordering information

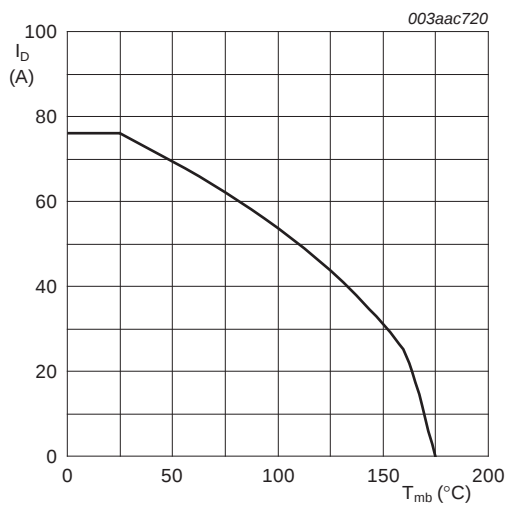
Type number	Package		
	Name	Description	Version
PSMN7R0-30YL	LPAK	plastic single-ended surface-mounted package (LPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

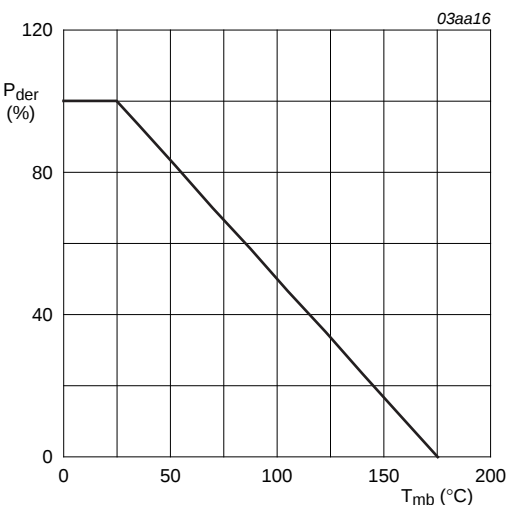
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	30	V
V_{DSM}	peak drain-source voltage	$t_p \leq 25\text{ ns}$; $f \leq 500\text{ kHz}$; $E_{DS(AL)} \leq 90\text{ nJ}$; pulsed	-	35	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	53	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	-	76	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 3	-	260	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	51	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	65	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	260	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; $I_D = 65\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped	-	21	mJ



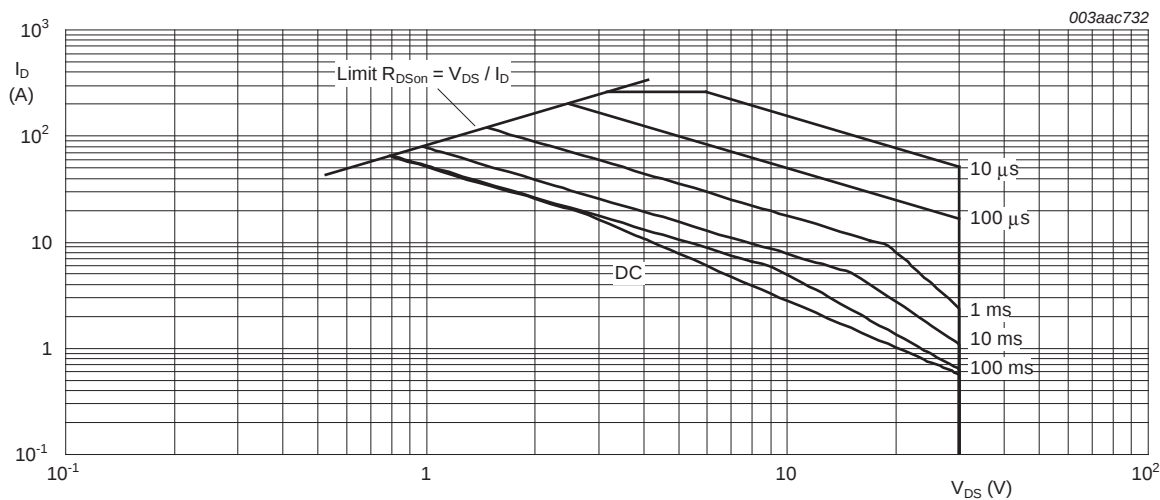
$V_{GS} \geq 10V$

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



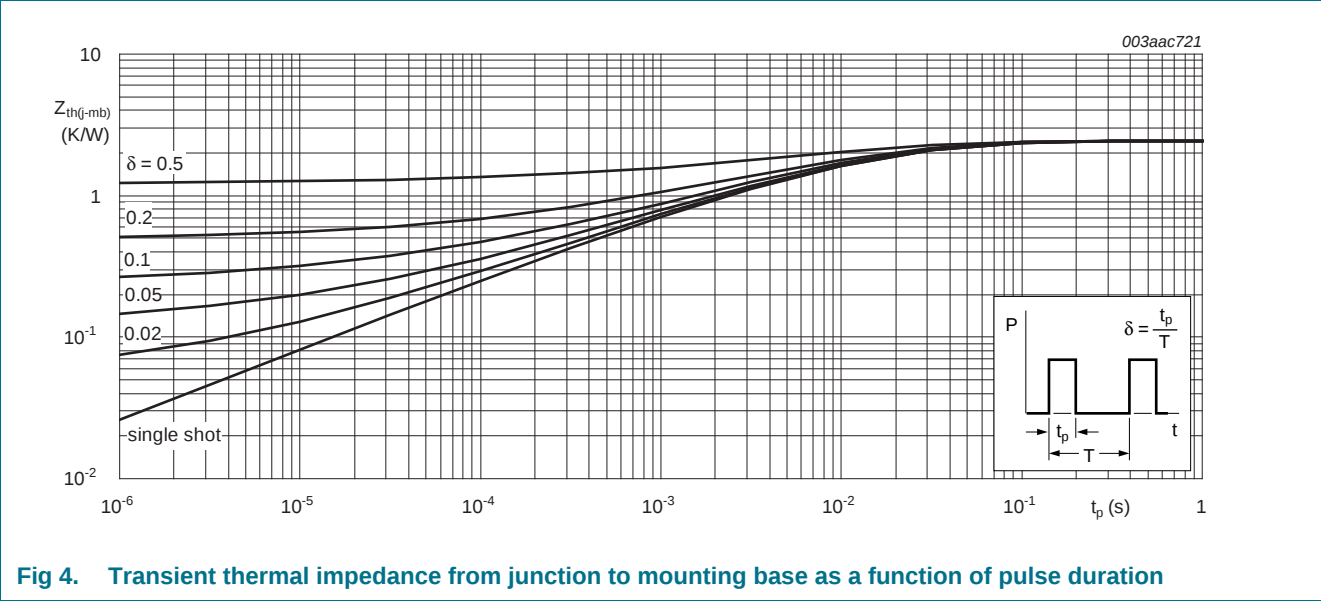
$T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.4	2.45	K/W



6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	30	-	-	V
		$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = -55\ ^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$; see Figure 11 ; see Figure 12	1.3	1.7	2.15	V
		$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = 150\ ^\circ C$; see Figure 12	0.65	-	-	V
		$I_D = 1\ mA$; $V_{DS} = V_{GS}$; $T_j = -55\ ^\circ C$; see Figure 12	-	-	2.45	V
I_{DSS}	drain leakage current	$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{DS} = 30\ V$; $V_{GS} = 0\ V$; $T_j = 150\ ^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
		$V_{GS} = -16\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\ V$; $I_D = 15\ A$; $T_j = 25\ ^\circ C$	-	6.97	9.1	mΩ
		$V_{GS} = 10\ V$; $I_D = 15\ A$; $T_j = 150\ ^\circ C$; see Figure 13	-	-	12.2	mΩ
		$V_{GS} = 10\ V$; $I_D = 15\ A$; $T_j = 25\ ^\circ C$	-	4.92	7	mΩ
R_G	gate resistance	$f = 1\ MHz$	-	0.6	1.5	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10\ A$; $V_{DS} = 12\ V$; $V_{GS} = 4.5\ V$; see Figure 14 ; see Figure 15	-	10	-	nC
		$I_D = 0\ A$; $V_{DS} = 0\ V$; $V_{GS} = 10\ V$	-	20	-	nC
		$I_D = 10\ A$; $V_{DS} = 12\ V$; $V_{GS} = 10\ V$; see Figure 14 ; see Figure 15	-	22	-	nC
Q_{GS}	gate-source charge	$I_D = 10\ A$; $V_{DS} = 12\ V$; $V_{GS} = 4.5\ V$; see Figure 14 ; see Figure 15	-	3.7	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.1	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.6	-	nC
Q_{GD}	gate-drain charge		-	2.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 12\ V$; see Figure 14 ; see Figure 15	-	2.6	-	V
C_{iss}	input capacitance	$V_{DS} = 12\ V$; $V_{GS} = 0\ V$; $f = 1\ MHz$; $T_j = 25\ ^\circ C$; see Figure 16	-	1270	-	pF
C_{oss}	output capacitance		-	255	-	pF
C_{rss}	reverse transfer capacitance		-	145	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\ V$; $R_L = 0.5\ \Omega$; $V_{GS} = 4.5\ V$; $R_{G(ext)} = 4.7\ \Omega$	-	24	-	ns
t_r	rise time		-	39	-	ns
$t_{d(off)}$	turn-off delay time		-	30	-	ns
t_f	fall time		-	11	-	ns

Table 6. Characteristics ...continued
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^{\circ}\text{C}$; see Figure 17	-	0.88	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	30	-	ns
Q_r	recovered charge	$V_{DS} = 20\text{ V}$	-	22	-	nC

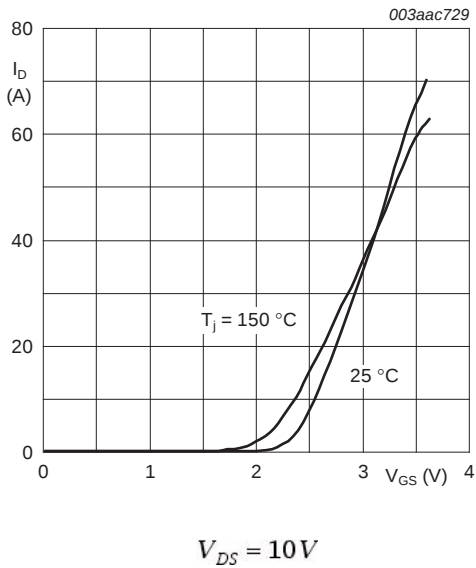


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

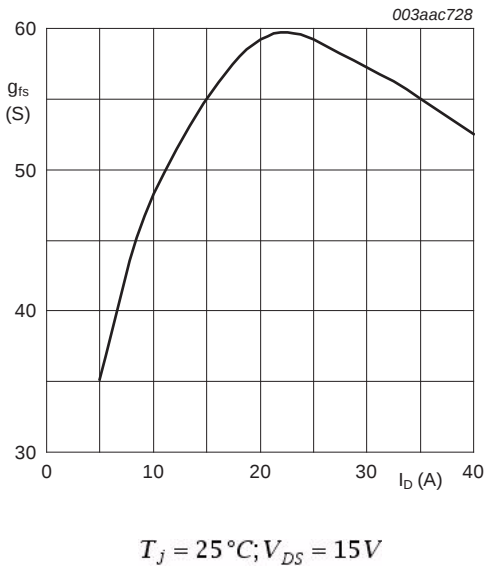


Fig 6. Forward transconductance as a function of drain current; typical values

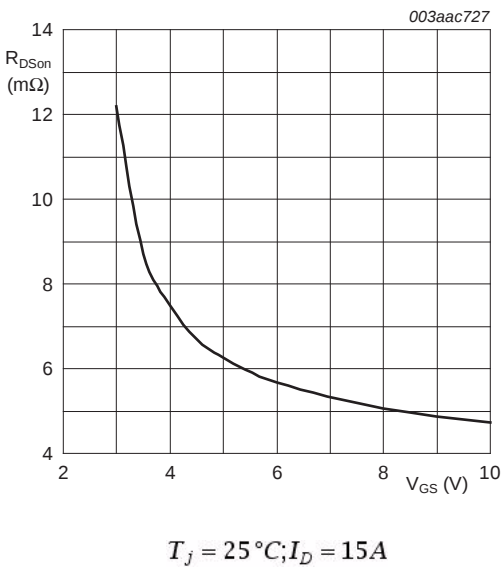


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

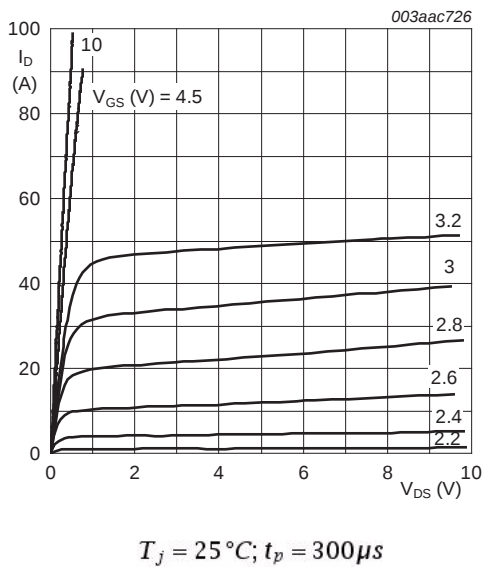
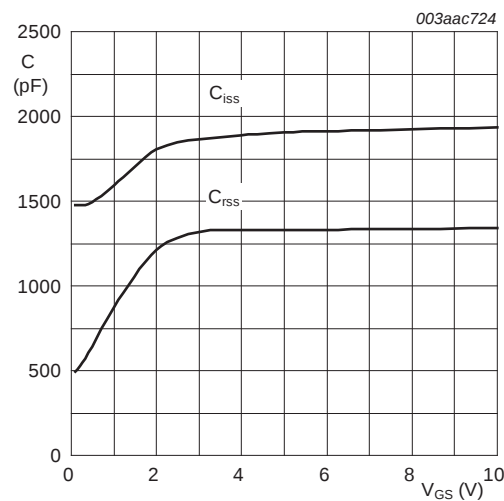
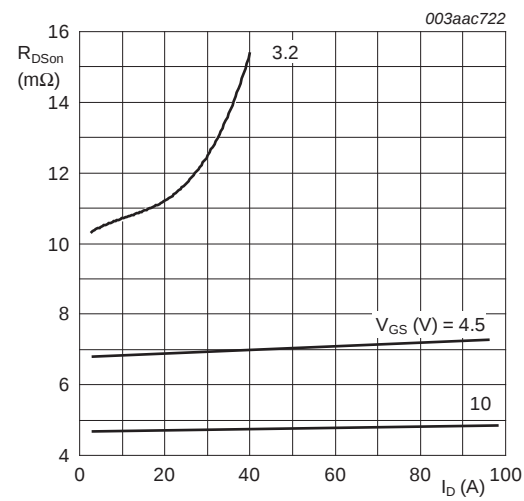


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



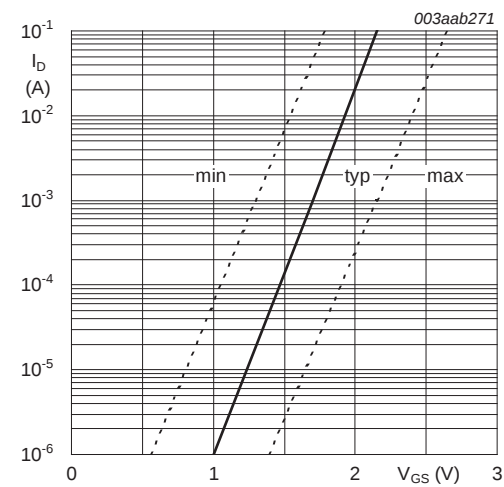
$V_{DS} = 0V; f = 1MHz$

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



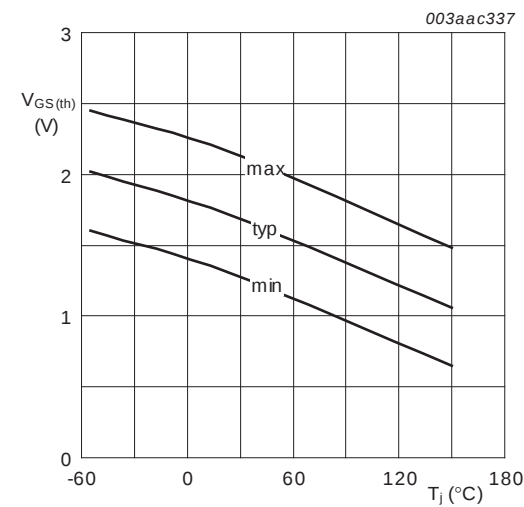
$T_j = 25^{\circ}C; t_p = 300\mu s$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



$T_j = 25^{\circ}C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$I_D = 1mA; V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature

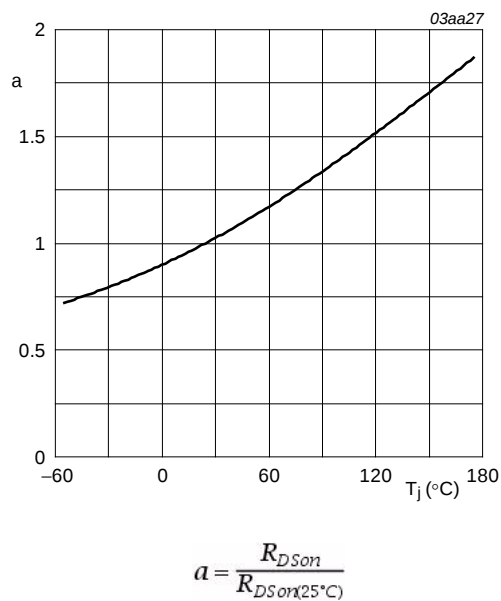


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

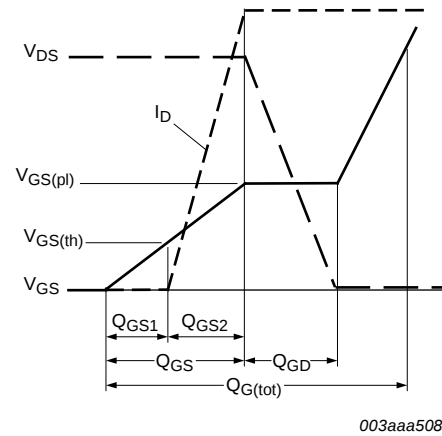


Fig 14. Gate charge waveform definitions

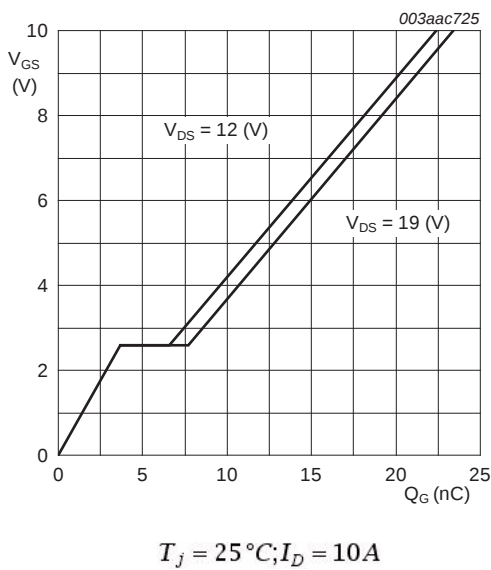


Fig 15. Gate-source voltage as a function of gate charge; typical values

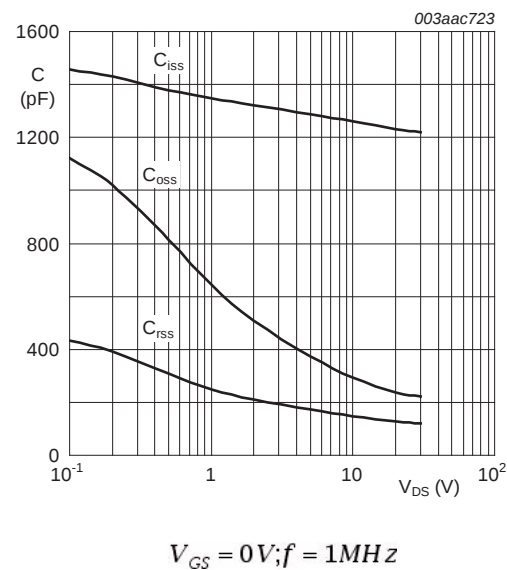


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

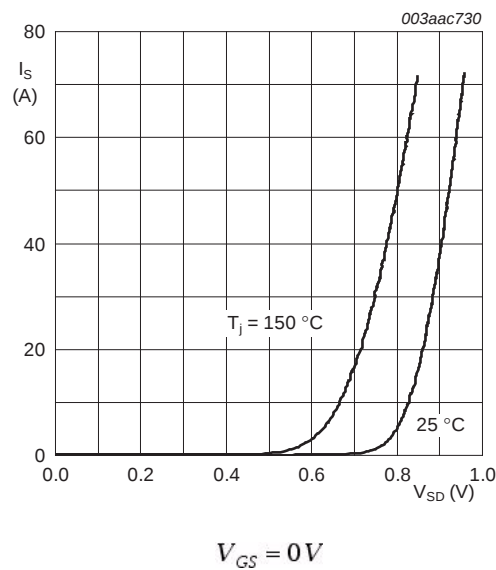


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

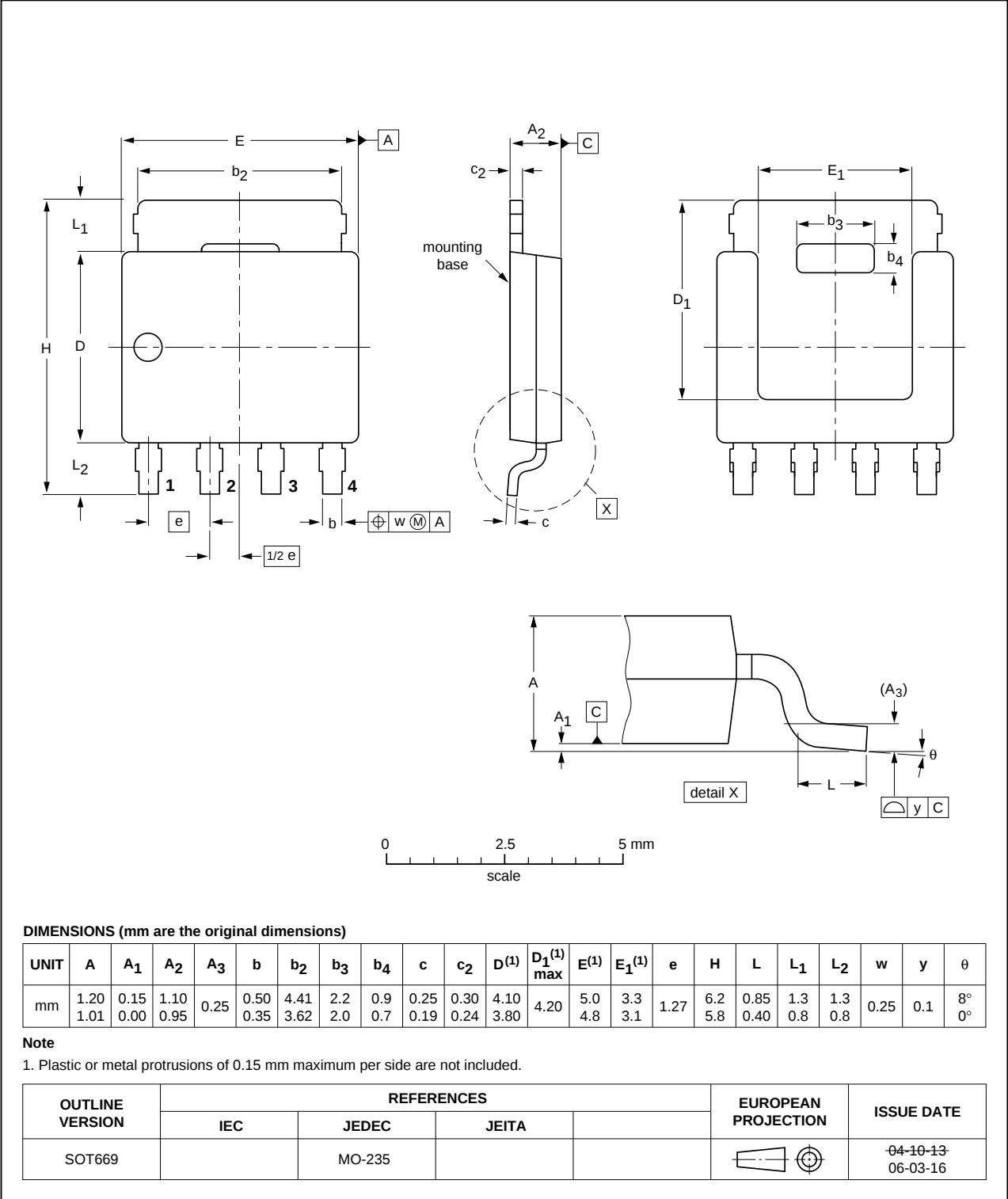


Fig 18. Package outline SOT669 (LPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-30YL v.4	20110309	Product data sheet	-	PSMN7R0-30YL v.3
Modifications:	• Various changes to content.			
PSMN7R0-30YL v.3	20100104	Product data sheet	-	PSMN7R0-30YL v.2
PSMN7R0-30YL v.2	20090105	Product data sheet	-	PSMN7R0-30YL v.1
PSMN7R0-30YL v.1	20081015	Preliminary data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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